## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1. (Currently Amended) A method of producing an oxide superconducting film comprising:

depositing, on a single-crystal substrate, substances scattered from a raw material due to irradiation with laser beams according to a pulsed-laser deposition method,

performing the irradiation of the raw material is in a manner such that the repetition frequency of the pulse irradiation of the laser beams is divided into at least two steps; a laser frequency of a second step being higher than the laser frequency of a first step and the laser frequency of the second step being less than 100 times the laser frequency of the first step.

wherein a power of the laser beams is greater than or equal to 400 mJ;

a temperature of the single-crystal substrate during the pulsed-laser deposition is more than or equal to 600 °C and less than 1,200 °C;

a gas pressure during the pulsed laser deposition is within the range of 1.33 Pa to 100 Pa; and

an atmospheric gas during the pulsed laser deposition contains oxygen.

2. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein the laser frequency of the second step is not less than 2 times and not more than 40 times as high as the laser frequency of the first step in a case where the laser frequency of the first step is greater than or equal to 1 Hz and less than 20 HZ; and the laser frequency of the second step is not less than 2 times and not more than 5 times as high as the laser frequency of the first step in the case where when the first laser frequency is 20 Hz;

wherein a power of the laser beams is greater than or equal to 400 mJ;

a temperature of the single-crystal substrate during the pulsed-laser deposition is more than or equal to  $600 \,^{\circ}\text{C}$  and less than  $1,200 \,^{\circ}\text{C}$ ;

a gas pressure during the pulsed laser deposition is within the range of  $1.33\ Pa$  to  $100\ Pa$ ; and

an atmospheric gas during the pulsed laser deposition contains oxygen.

- 3.-5. (Cancelled).
- 6. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to [[100]] 66.66 Pa.
- 7. (Currently Amended) A method of producing an oxide superconducting film according to claim [[6]] 2, wherein a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to 66.66 Pa.
  - 8. 15 (Cancelled).
- 16. (Previously presented) A method of producing an oxide superconducting film according to claim 1, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.
- 17. (Currently Amended) A method of producing an oxide superconducting film according to claim [[3]] 2, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.
- 18. (Currently Amended) A method of producing an oxide superconducting film according to claim [[4]] 6, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.
- 19. (Currently Amended) A method of producing an oxide superconducting film according to claim [[6]] 7, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.

- 20. (Cancelled).
- 21. (New) The method of producing an oxide superconducting film according to claim 1, wherein the power of the laser beam is greater than or equal to 500 mJ.
- 22. (New) The method of producing an oxide superconducting film according to claim 2, wherein the power of the laser beams is greater than or equal to 500 mJ.